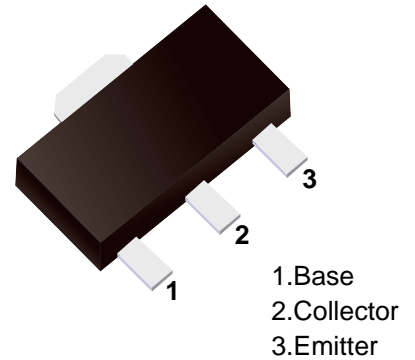


■ **NPN Transistors**

■ **Features**

- NPN transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SB772



■ **Simplified outline(SOT-89)**

■ **Absolute Maximum Ratings Ta = 25°C**

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V _{CB0}	40	V
Collector to Emitter Voltage	V _{CE0}	30	V
Emitter to Base Voltage	V _{EB0}	6	V
Collector Current to Continuous	I _c	3	A
Collector Dissipation	P _c	0.5	W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-55 to 150	°C

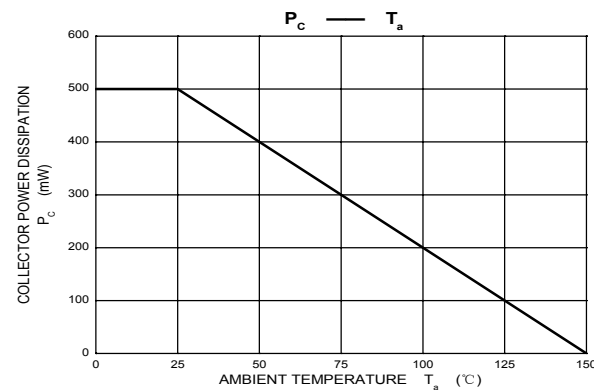
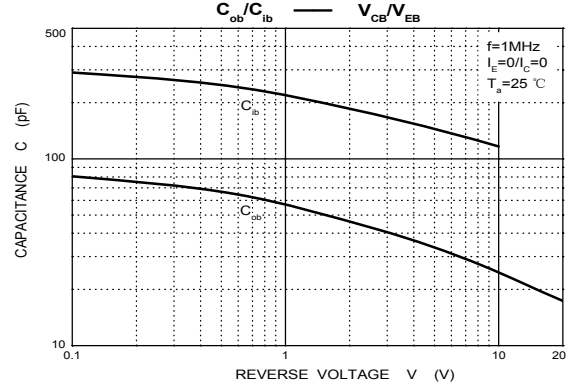
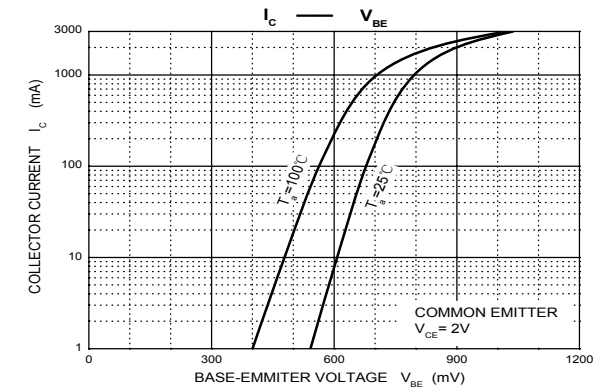
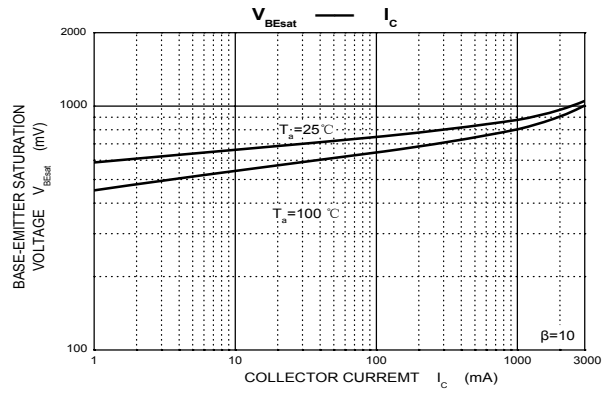
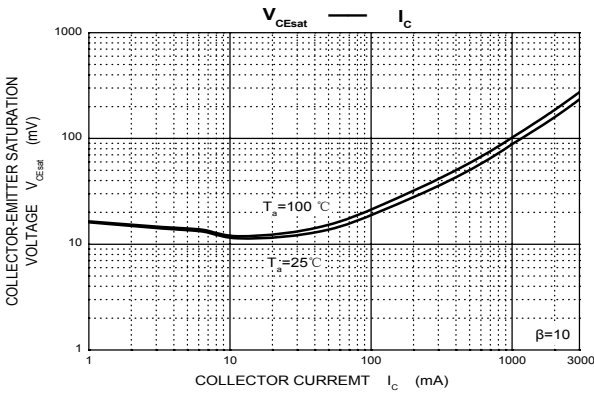
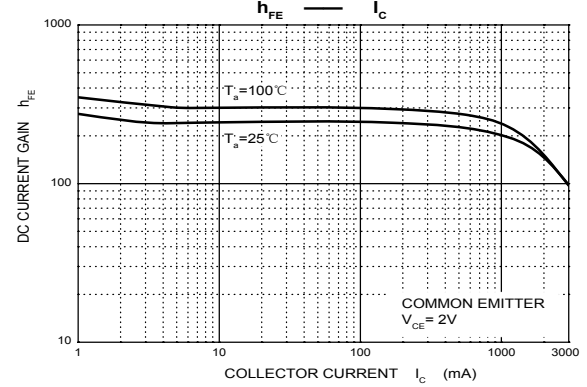
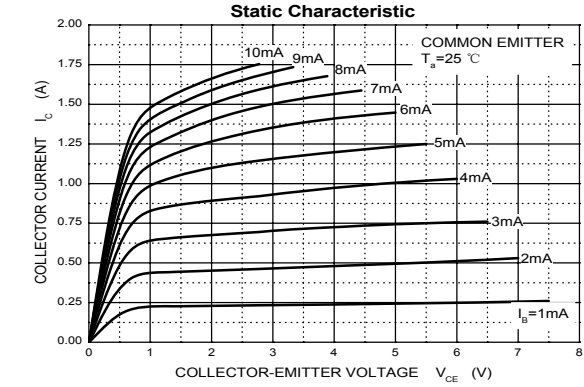
■ **Electrical Characteristics Ta = 25°C**

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CB0}	I _c =100uA , I _E =0	40			V
Collector-emitter breakdown voltage	V _{CE0}	I _c = 10 mA , I _B =0	30			V
Emitter-base breakdown voltage	V _{EB0}	I _E = 100 uA , I _c =0	6			V
Collector cut-off current	I _{CB0}	V _{CB} =40 V , I _E =0			1	uA
Collector cut-off current	I _{CE0}	V _{CE} =30 V , I _B =0			10	uA
Emitter cut-off current	I _{EB0}	V _{EB} =6V , I _c =0			1	uA
DC current gain	h _{FE}	V _{CE} = 2V, I _c = 1A	60		400	
		V _{CE} =2V, I _c = 100mA	32			
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =2A, I _B = 0.2A			0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _c =2A, I _B = 0.2A			1.5	V
Transition frequency	f _T	V _{CE} =5 V, I _c =0.1mA, f = 10MHz	50			MHz

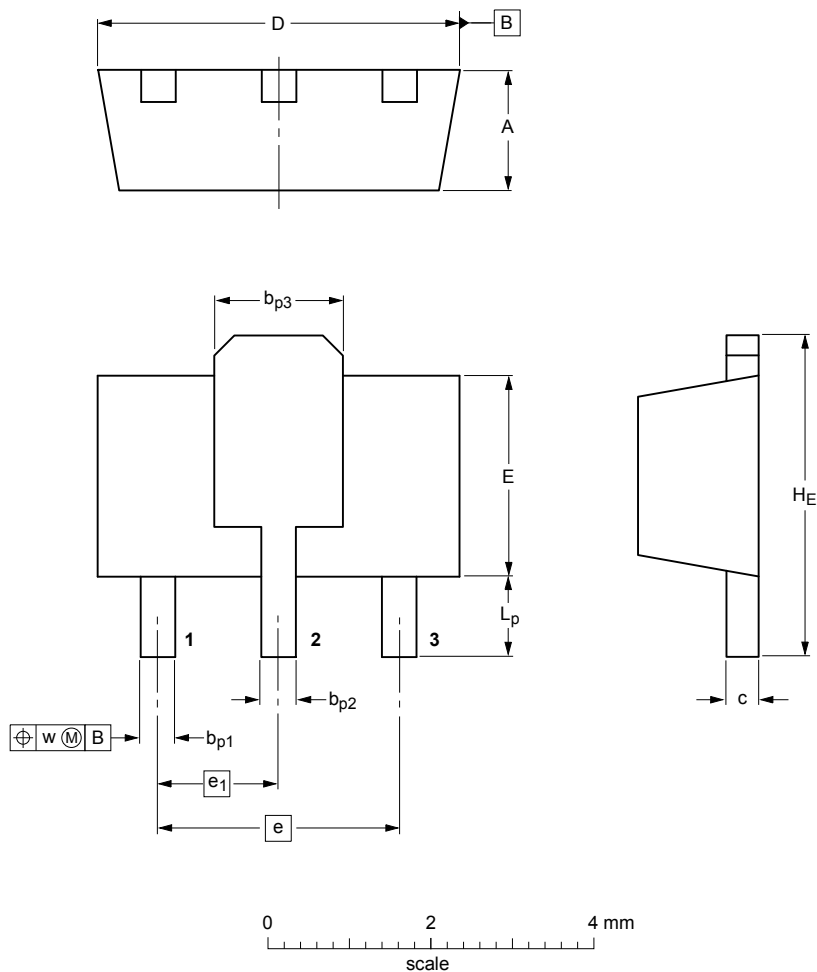
■ **Classification of h_{FE}(1)**

Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400

■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4			3.75	0.8	